Lead-free Green

## Product Summary

| BV DSS $^{*} 30 \mathrm{~V}$ | $\mathbf{R}_{\mathrm{DS}(\mathrm{ON})}$ Max | $\mathrm{ID}_{\mathrm{D}}$ Max <br> $\mathbf{T}_{\mathbf{A}}=25^{\circ} \mathbf{C}$ |
| :---: | :---: | :---: |
|  | $12 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{GS}}=10 \mathrm{~V}$ | 10 A |
|  | $16 \mathrm{~m} \Omega @ \mathrm{~V}_{\mathrm{GS}}=4.5 \mathrm{~V}$ | 8.5 A |

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $\mathrm{R}_{\mathrm{DS}(\mathrm{ON})}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters


## Features and Benefits

- 0.6 mm profile - Ideal for Low Profile Applications
- PCB Footprint of $4 \mathrm{~mm}^{2}$
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free \& Fully RoHS Compliant (Notes 1 \& 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability


## Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)


## U-DFN2020-6 (Type F)



Top View


Bottom View


Pin Out
Bottom View


Equivalent Circuit

## Ordering Information (Note 4)

| Part Number | Case | Packaging |
| :---: | :---: | :---: |
| DMN3016LFDF-7 | U-DFN2020-6 (Type F) | $3,000 /$ Tape \& Reel |
| DMN3016LFDF-13 | U-DFN2020-6 (Type F) | $10,000 /$ Tape \& Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) \& 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen-and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain $<900 \mathrm{ppm}$ bromine, $<900 \mathrm{ppm}$ chlorine ( $<1500 \mathrm{ppm}$ total $\mathrm{Br}+\mathrm{Cl}$ ) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



NZ = Product Type Marking Code
YM = Date Code Marking
$Y=Y e a r(e x: D=2016)$
M = Month (ex: 9 = September)
Date Code Key

| Year | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Code | D | E | F | G | H | I | J | K |  |  |  |  |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings $\left(@ T_{A}=+25^{\circ} \mathrm{C}\right.$, unless otherwise specified.)

| Characteristic |  |  | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Drain-Source Voltage |  |  | $V_{\text {DSS }}$ | 30 | V |
| Gate-Source Voltage |  |  | $\mathrm{V}_{\text {GSS }}$ | $\pm 20$ | V |
| Continuous Drain Current (Note 6) VGS $=10 \mathrm{~V}$ | Steady State | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{A}}=+70^{\circ} \mathrm{C} \\ & \hline \end{aligned}$ | ID | $\begin{gathered} \hline 10 \\ 8 \\ \hline \end{gathered}$ | A |
|  | t<10s | $\begin{aligned} & \mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{A}}=+70^{\circ} \mathrm{C} \\ & \hline \end{aligned}$ | ID | $\begin{gathered} \hline 12 \\ 9 \\ \hline \end{gathered}$ | A |
| Maximum Continuous Body Diode Forward Current (Note 6) |  |  | Is | 2.5 | A |
| Pulsed Drain Current (10 $\mu$ s Pulse, Duty Cycle $=1 \%$ ) |  |  | IDM | 50 | A |
| Avalanche Current (Note 7) L $=0.1 \mathrm{mH}$ |  |  | $\mathrm{I}_{\text {AR }}$ | 22 | A |
| Avalanche Energy (Note 7) L $=0.1 \mathrm{mH}$ |  |  | $\mathrm{E}_{\text {AR }}$ | 24 | mJ |

Thermal Characteristics $\left(@ T_{\mathrm{A}}=+25^{\circ} \mathrm{C}\right.$, unless otherwise specified.)

| Characteristic |  | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Total Power Dissipation (Note 5) | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | PD | 0.73 | W |
|  | $\mathrm{T}_{\mathrm{A}}=+70^{\circ} \mathrm{C}$ |  | 0.47 |  |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | $\mathrm{R}_{\theta \mathrm{JA}}$ | 174 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | $\mathrm{t}<10 \mathrm{~s}$ |  | 121 |  |
| Total Power Dissipation (Note 6) | $\mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}$ | PD | 2.02 | W |
|  | $\mathrm{T}_{\mathrm{A}}=+70^{\circ} \mathrm{C}$ |  | 1.30 |  |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $\mathrm{R}_{\theta \mathrm{JA}}$ | 66 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  | t<10s |  | 42 |  |
| Thermal Resistance, Junction to Case (Note 6) | Steady State | $\mathrm{R}_{\text {өJ }}$ | 11.6 |  |
| Operating and Storage Temperature Range |  | $\mathrm{T}_{\mathrm{J}, \mathrm{T}_{\text {STG }}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Electrical Characteristics (@T $A=+25^{\circ} \mathrm{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS (Note 8) |  |  |  |  |  |  |
| Drain-Source Breakdown Voltage | BV ${ }_{\text {DSS }}$ | 30 | - | - | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |
| Zero Gate Voltage Drain Current | ldss | - | - | 1 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{DS}}=30 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}$ |
| Gate-Source Leakage | IGss | - | - | $\pm 100$ | nA | $\mathrm{V}_{\mathrm{GS}}= \pm 20 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0 \mathrm{~V}$ |
| ON CHARACTERISTICS (Note 8) |  |  |  |  |  |  |
| Gate Threshold Voltage | $\mathrm{V}_{\mathrm{GS}}(\mathrm{TH})$ | 1.4 | - | 2.0 | V | $\mathrm{V}_{\mathrm{DS}}=\mathrm{V}_{\mathrm{GS}}, \mathrm{I}_{\mathrm{D}}=250 \mu \mathrm{~A}$ |
| Static Drain-Source On-Resistance | RDS(ON) | - | 8 | 12 | $\mathrm{m} \Omega$ | $\mathrm{V}_{\mathrm{GS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=11 \mathrm{~A}$ |
|  |  | - | 12 | 16 |  | $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=9 \mathrm{~A}$ |
| Diode Forward Voltage | $V_{\text {SD }}$ | - | 0.70 | 1.0 | V | $\mathrm{V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{IS}=1 \mathrm{~A}$ |
| DYNAMIC CHARACTERISTICS (Note 9) |  |  |  |  |  |  |
| Input Capacitance | $\mathrm{C}_{\text {iss }}$ | - | 1415 | - | pF | $\begin{aligned} & V_{\mathrm{DS}}=15 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \\ & \mathrm{f}=1.0 \mathrm{MHz} \end{aligned}$ |
| Output Capacitance | $\mathrm{C}_{\text {oss }}$ | - | 119 | - |  |  |
| Reverse Transfer Capacitance | $\mathrm{Crss}^{\text {s }}$ | - | 82 | - |  |  |
| Gate Resistance | $\mathrm{R}_{\mathrm{g}}$ | - | 2.6 | - | $\Omega$ | $\mathrm{V}_{\mathrm{DS}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0 \mathrm{~V}, \mathrm{f}=1.0 \mathrm{MHz}$ |
| Total Gate Charge ( $\mathrm{V}_{\mathrm{GS}}=4.5 \mathrm{~V}$ ) | $\mathrm{Q}_{\mathrm{g}}$ | - | 11.3 | - | nC | $V_{D S}=15 \mathrm{~V}, \mathrm{ld}=12 \mathrm{~A}$ |
| Total Gate Charge (VGS = 10V) | $\mathrm{Q}_{\mathrm{g}}$ | - | 25.1 | - |  |  |
| Gate-Source Charge | $\mathrm{Q}_{\mathrm{gs}}$ | - | 3.5 | - |  |  |
| Gate-Drain Charge | $\mathrm{Q}_{\mathrm{gd}}$ | - | 3.6 | - |  |  |
| Turn-On Delay Time | $t_{\text {( }}^{\text {(ON }}$ ) | - | 4.8 | - | ns | $\begin{aligned} & V_{D D}=15 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=10 \mathrm{~V}, \\ & \mathrm{R}_{\mathrm{L}}=1.25 \Omega, \mathrm{R}_{\mathrm{g}}=3 \Omega \end{aligned}$ |
| Turn-On Rise Time | $\mathrm{t}_{\mathrm{R}}$ | - | 16.5 | - |  |  |
| Turn-Off Delay Time | to(OFF) | - | 26.1 | - |  |  |
| Turn-Off Fall Time | $\mathrm{t}_{\mathrm{F}}$ | - | 5.6 | - |  |  |
| Reverse Recovery Time | $\mathrm{t}_{\mathrm{RR}}$ | - | 12.3 | - | ns | $\mathrm{lF}=12 \mathrm{~A}, \mathrm{di} / \mathrm{dt}=500 \mathrm{~A} / \mu \mathrm{s}$ |
| Reverse Recovery Charge | QRR | - | 10.4 | - | nC |  |

Notes: 5. Device mounted on FR-4 substrate PC board, 2 oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2 oz copper, with 1inch square copper plate.
7. $I_{A S}$ and $E_{A S}$ rating are based on low frequency and duty cycles to keep $T_{J}=+25^{\circ} \mathrm{C}$.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

DMN3016LFDF


Fig. 1 Typical Output Characteristics


Fig. 3 Typical On-Resistance vs.
Drain Current and Gate Voltage


Fig. 5 On-Resistance Variation with Temperature

$\mathrm{V}_{\mathrm{GS}}$, GATE-SOURCE VOLTAGE (V)
Fig. 2 Typical Transfer Characteristics


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature


Fig. 6 On-Resistance Variation with Temperature


Fig. 7 Gate Threshold Variation vs. Ambient Temperature


Fig. 9 Typical Junction Capacitance


Fig. 8 Diode Forward Voltage vs. Current


Fig. 10 Gate-Charge Characteristics


DMN3016LFDF

## Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.
U-DFN2020-6 (Type F)


| U-DFN2020-6 <br> (Type F) |  |  |  |
| :---: | :---: | :---: | :---: |
| Dim | Min | Max | Typ |
| A | 0.57 | 0.63 | 0.60 |
| A1 | 0.00 | 0.05 | 0.03 |
| A3 | - | - | 0.15 |
| b | 0.25 | 0.35 | 0.30 |
| D | 1.95 | 2.05 | 2.00 |
| D2 | 0.85 | 1.05 | 0.95 |
| D2a | 0.33 | 0.43 | 0.38 |
| E | 1.95 | 2.05 | 2.00 |
| E2 | 1.05 | 1.25 | 1.15 |
| E2a | 0.65 | 0.75 | 0.70 |
| e | 0.65 BSC |  |  |
| e2 | 0.863 BSC |  |  |
| e3 | 0.70 BSC |  |  |
| e4 | 0.325 BSC |  |  |
| k | 0.37 BSC |  |  |
| k1 | 0.15 BSC |  |  |
| k2 | 0.36 BSC |  |  |
| L | 0.225 | 0.325 | 0.275 |
| z | 0.20 BSC |  |  |
| z1 | 0.110 BSC |  |  |
| z2 | 0.20 BSC |  |  |
| All Dimensions in mm |  |  |  |

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.
U-DFN2020-6 (Type F)


| Dimensions | Value <br> (in mm) |
| :---: | :---: |
| $\mathbf{C}$ | 0.650 |
| $\mathbf{X}$ | 0.400 |
| $\mathbf{X 1}$ | 0.480 |
| $\mathbf{X 2}$ | 0.950 |
| $\mathbf{X 3}$ | 1.700 |
| $\mathbf{Y}$ | 0.425 |
| $\mathbf{Y 1}$ | 0.800 |
| $\mathbf{Y 2}$ | 1.150 |
| $\mathbf{Y 3}$ | 1.450 |
| $\mathbf{Y 4}$ | 2.300 |

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